

Absorption and Carrier Transport Properties of Doped Hematite

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Abstract : Hematite (Fe_2O_3), commonly known as 'rust' which usually surfaced on metal when exposed to some climatic materials. This emerges as a promising candidate for photoelectrochemical (PEC) water splitting due to its favorable physiochemical properties of the narrow band gap (2.1-2.2 eV), chemical stability, nontoxicity, abundance, and low cost. However, inherent limitations such as short hole diffusion length (2-4 nm), high charge recombination rate, and slow oxygen evolution reaction kinetics inhibit the PEC performances of $\alpha\text{-Fe}_2\text{O}_3$ photoanodes. As such, given the narrow bandgap enabling excellent optical absorption, increased charge carrier density and accelerated surface oxidation reaction kinetics become the key points for improved photoelectrochemical performances for $\alpha\text{-Fe}_2\text{O}_3$ photoanodes and metal ion doping as an effective way to promote charge transfer by increasing donor density and improving the electronic conductivity of $\alpha\text{-Fe}_2\text{O}_3$. Hematite attracts enormous efforts with a number of metal ions (Ti, Zr, Sn, Pt ,etc.) as dopants. A facile deposition-annealing process showed greatly enhanced PEC performance due to the increased donor density and reduced electron-hole recombination at the time scale beyond a few picoseconds. Zr doping was also found to enhance the PEC performance of $\alpha\text{-Fe}_2\text{O}_3$ nanorod arrays by reducing the rate of electron-hole recombination. Slow water oxidation reaction kinetics, another main factor limiting the PEC water splitting efficiency of $\alpha\text{Fe}_2\text{O}_3$ as photoanodes, was previously found to be effectively improved by surface treatment.

Keywords : deposition-annealing, hematite, metal ion doping, nanorod

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